



DMMT5551/DMMT5551S

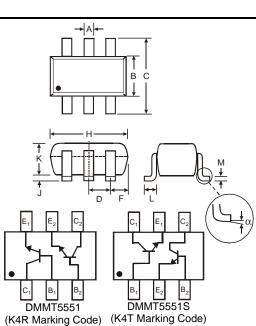
MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

## Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DMMT5401)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, hFE, VCE(SAT), VBE(SAT)
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)

## **Mechanical Data**

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4R & K4T, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



SOT-26									
Dim	Min	Max	Тур						
Α	0.35	0.50	0.38						
В	1.50	1.70	1.60						
С	2.70	3.00	2.80						
D	_		0.95						
F	_	_	0.55						
Н	2.90	3.10	3.00						
J	0.013	0.10	0.05						
Κ	1.00	1.30	1.10						
L	0.35	0.55	0.40						
М	0.10	0.20	0.15						
α	0°	8°							
All D	Dimens	ions in	mm						

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current - Continuous (Note 2)	Ι <sub>C</sub>	200	mA
Power Dissipation (Note 2, 3)	Pd	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	R <sub>0JA</sub>	417	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: Built with adjacent die from a single wafer. 1.

Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our 2. website at http://www.diodes.com/datasheets/ap02001.pdf.

3. Maximum combined dissipation.

No purposefully added lead. 4

5.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date 6. Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



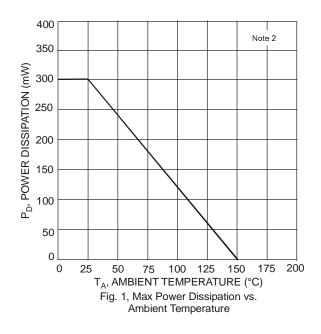
#### **Electrical Characteristics** $@T_A = 25^{\circ}C$ unless otherwise specified

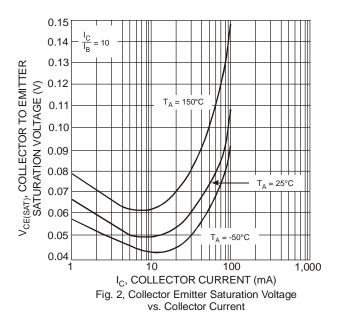
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Cymbol		max	Unit	
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	180		V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	160		V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0		V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector Cutoff Current	I <sub>СВО</sub>	_	50	nA μA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0 V <sub>CB</sub> = 120V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	50	nA	$V_{EB} = 4.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 7)					
DC Current Gain (Note 8)	hFE	80 80 30	 250 	_	$I_{C} = 1.0mA, V_{CE} = 5.0V$ $I_{C} = 10mA, V_{CE} = 5.0V$ $I_{C} = 50mA, V_{CE} = 5.0V$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.15 0.20	V	$I_{C} = 10$ mA, $I_{B} = 1.0$ mA $I_{C} = 50$ mA, $I_{B} = 5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	1.0	V	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	_	6.0	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$
Small Signal Current Gain	h <sub>FE</sub>	50	250	—	$V_{CE} = 10V, I_{C} = 1.0mA,$ f = 1.0kHz
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = 10V$ , $I_C = 10mA$ , f = 100MHz
Noise Figure	NF		8.0	dB	$\label{eq:Vce} \begin{split} V_{CE} &= 5.0 \text{V}, \ \text{I}_{C} = 200 \mu \text{A}, \\ \text{R}_{S} &= 1.0 \text{k} \Omega, \ \text{f} = 1.0 \text{k} \text{Hz} \end{split}$

Notes:

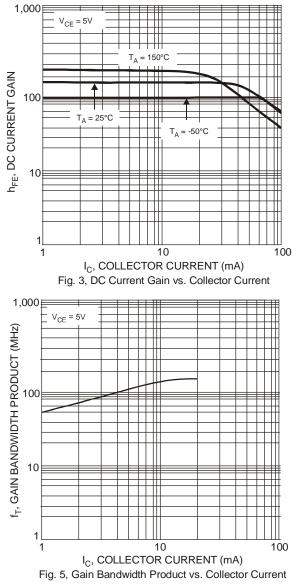
7.

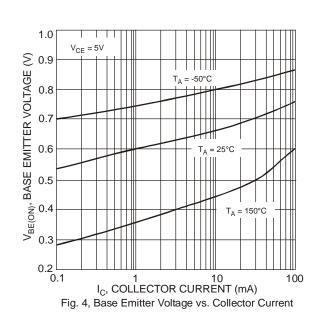
Short duration pulse test used to minimize self-heating effect. The DC Current Gain,  $h_{FE}$ , (matched at  $I_C = 10$ mA and  $V_{CE} = 5$ V) Collector Emitter Saturation Voltage,  $V_{CE(SAT)}$ , and Base Emitter Saturation Voltage,  $V_{BE(SAT)}$  are matched with typical matched tolerances of 1% and maximum of 2%. 8.











# Ordering Information (Note 6 & 9 )

Device	Packaging	Shipping		
DMMT5551-7-F	SOT-26	3000/Tape & Reel		
DMMT5551S-7-F	SOT-26	3000/Tape & Reel		

Notes: 9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



K4R = DMMT5551 Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September



 $\begin{array}{l} \mathsf{K4T} = \mathsf{DMMT5551S} \ \mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} = \mathsf{Year} \ \mathsf{ex} : \mathsf{T} = 2006 \\ \mathsf{M} = \mathsf{Month} \ \mathsf{ex} : \mathsf{9} = \mathsf{September} \end{array}$ 

Date Code Key

Year	2003	2004	4 20	005	2006	2007	2008	2009	9 20	010	2011	2012
Code	Р	R		S	Т	U	V	W		Х	Y	Z
	1			I	Т	1	I	I	I	Т		
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	1	5	6	7	8	0	0	N	П



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